Data sheet acquired from Harris Semiconductor SCHS056

## **CMOS OR Gates**

High-Voltage Types (20-Volt Rating)

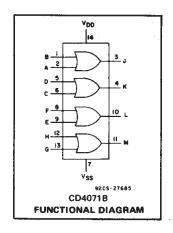
CD4071B Quad 2-Input OR Gate CD4072B Dual 4-Input OR Gate CD4075B Triple 3-Input OR Gate

CD4071B, CD4072B, and CD4075B OR gates provide the system designer with direct implementation of the positive-logic OR function and supplement the existing family of CMOS gates. The CD4071, CD4072, and CD4075 types are supplied in 14-lead dual-in-line ceramic packages (D and F suffixes), 14-lead dual-in-line plastic packages (E suffix), and in chip form (H suffix).

## CD4071B, CD4072B, CD4075B Types

### Features:

- Medium-Speed Operation-tpLH, tpHL = 60 ns (typ.) at V<sub>DD</sub> = 10 V
- 100% tested for quiescent current at 20 V
- Maximum input current of 1 μA at 18 V over full package-temperature range; 100 nA at 18 V and 25 °C
- Standardized, symmetrical output characteristics
- Noise margin (over full package temperature range)
  - 1 V at V<sub>DD</sub> = 5 V 2 V at V<sub>DD</sub> = 10 V 2.5 V at V<sub>DD</sub> = 15 V
- 5-V, 10-V, and 15-V parametric ratings
- Meets all requirements of JEDEC Tentative Standard No. 13B, "Standard Specifications for Description of 'B' Series CMOS Devices"



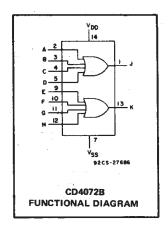
### **RECOMMENDED OPERATING CONDITIONS**

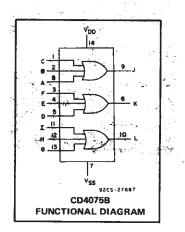
For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	LIN	UNITS	
	MIN.	MAX.	
Supply-Voltage Range (For TA = Full Package-Temperature Range)	3	18	٧

### STATIC ELECTRICAL CHARACTERISTICS

CHARACTER-	CONDITIONS			LIMITS AT INDICATED TEMPERATURES (°C)							
ISTIC	Vo	VIN	V <sub>DD</sub>					+25			UNITS
	(V)	(V)		-55	-40	+85	+125	Min.	Тур.	Max.	
Quiescent Device		0,5	5	0.25	0.25	7.5	7.5	_	0.01	0.25	μΑ
Current,	-	0,10	10	0.5	0.5	15	15	-	0.01	0.5	
IDD Max.	-	0,15	15	1	1	30	30	-	0.01	1	
		0,20	20	5	5	150	150	-	0.02	5	
Output Low	0.4	0,5	5	0.64	0.61	0.42	0,36	0.51	1	-	
(Sink) Current	0.5	0,10	10	1.6	1.5	1.1	0.9	1.3	2.6	-	
IOL Min.	1.5	0,15	15	4.2	4	2.8	2.4	3.4	6.8	_	
Output High	4.6	0,5	5	-0.64	-0.61	-0.42	-0.36	-0.51	-1	_	mA
(Source)	2.5	0,5	5	-2	-1.8	-1.3	-1.15	-1.6	-3.2	-	
Current, IOH Min.	9.5	0,10	10	-1.6	-1.5	-1.1	-0.9	-1.3	-2.6	-	
TOH WIIII.	13.5	0,15	15	-4.2	-4	-2.8	-2.4	-3.4	6.8	-	
Output Voltage:	-	0,5	5	0.05					0	0.05	
Low-Level, VOI Max.	_	0,10	10	0.05				-	0	0.05	v
VOL WAX.	_	0,15	15	0.05					0	0.05	
Output Voltage:		0,5	5	4.95			4.95	5	_	•	
High-Level,	_	0,10	10	9.95				9.95	10	-	
VOH Min.		0,15	15	14.95				14.95	15	-	
Input Low Voltage, VIL Max. Input High	0.5, 4.5		. 5	1.5				_	Γ-	1.5	
	1, 9	_	10	3				-	_	3	- v
	1.5,13.5	÷	15	4				_	_	4	
	4.5	_	5	3.5				3.5			
Voltage,	9	, ,	10	7 .				7			
VIH Min.	13.5	_	15	11				11	<u> </u>	_	
Input Current I <sub>IN</sub> Max.	ž.	0,18	18	±0.1	±0.1	±1	±1	<u>-</u> .	±10 <sup>-5</sup>	±0.1	μΑ





# CD4071B, CD4072B, CD4075B Types

MAXIMUM RATINGS, Absolute-Maximum Values:	
DC SUPPLY-VOLTAGE RANGE, (VDD)	'
Voltages referenced to VSS Terminal)0.5\	/ to +20V
INPUT VOLTAGE RANGE, ALL INPUTS0.5V to V	+0.5V
DC INPUT CURRENT, ANY ONE INPUT	
POWER DISSIPATION PER PACKAGE (PD):	
For T <sub>A</sub> = -55°C to +100°C	500mW
For T <sub>A</sub> = +100°C to +125°C	200mW
DEVICE DISSIPATION PER OUTPUT TRANSISTOR	
FOR TA = FULL PACKAGE-TEMPERATURE RANGE (All Package Types)	100mW
OPERATING-TEMPERATURE RANGE (TA)55°C to	+125°C
STORAGE TEMPERATURE RANGE (Tstg)65°C to	+150°C
LEAD TEMPERATURE (DURING SOLDERING):	
At distance 1/16 $\pm$ 1/32 inch (1.59 $\pm$ 0.79mm) from case for 10s max	+265°C

# DYNAMIC ELECTRICAL CHARACTERISTICS at T\_A = 25°C, Input t\_r, t\_f = 20 ns, and C\_L = 50 pF, R\_L = 200 $~k\Omega$

CHARACTERISTIC	TEST COND	TIONS	ALL.	UNITS	
		V <sub>DD</sub> VOLTS	TYP.	MAX.	
Propagation Delay Time, <sup>t</sup> PHL, <sup>t</sup> PLH		5 10 15	125 60 45	250 120 90	ns
Transition Time, <sup>t</sup> THL <sup>, t</sup> TLH		5 10 15	100 50 40	200 100 80	ns
Input Capacitance, C <sub>IN</sub>	Any Input	1 – 1	5	7.5	pF

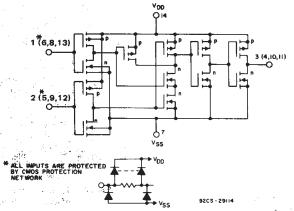


Fig. 3 - Schematic diagram for CD4071B (1 of 4 identical gates).

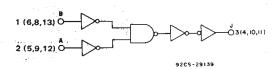


Fig. 5 -/ Logic diagram for CD4071B (1 of 4 identical gates).

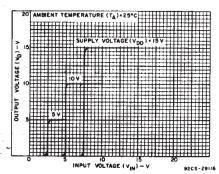


Fig. 1 — Typical voltage transfer characteristics

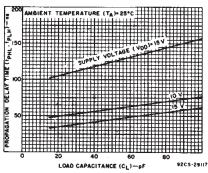


Fig. 2 — Typical propagation delay time as a function of load capacitance.

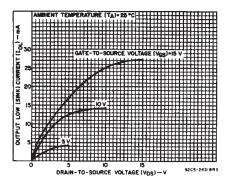


Fig. 4 — Typical output low (sink) current characteristics.

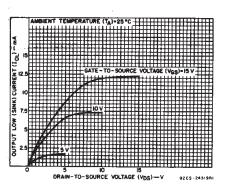
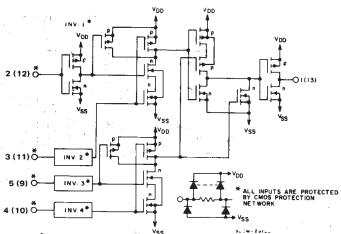


Fig. 6 — Minimum output low (sink) current characteristics.

### CD4071B, CD4072B, CD4075B Types



INVERTERS 2,3 AND 4 ARE IDENTICAL TO INVERTER 1.

Fig. 7 - Schematic diagram for CD4072B (1 of 2 identical gates).

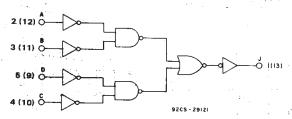


Fig. 9 - Logic diagram for CD4072B (1 of 2 identical gates).

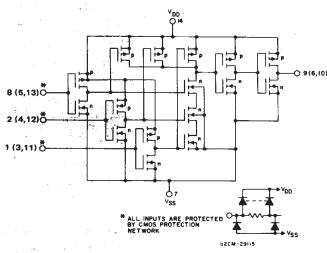


Fig. 11 - Schematic diagram for CD4075B (1 of 3 identical gates).

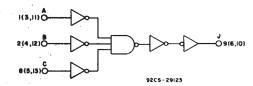


Fig. 13 - Logic diagram for CD4075B (1 of 3 identical gates).

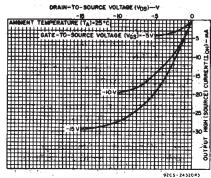


Fig. 8 — Typical output high (source) current characteristics.

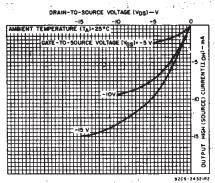


Fig. 10 – Minimum output high (source) current characteristics.

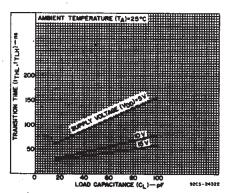


Fig. 12 — Typical transition time as a function of load capacitance.

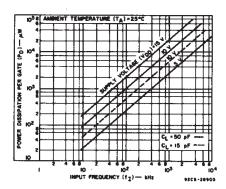
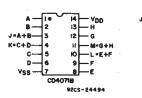
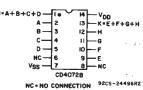


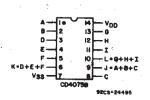
Fig. 14 – Typical dyanamic power dissipation as a function of frequency.

# CD4071B, CD4072B, CD4075B Types

### **TERMINAL ASSIGNMENTS (TOP VIEW)**







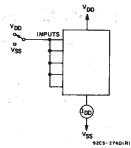


Fig. 15 - Quiescent device current test circuit.

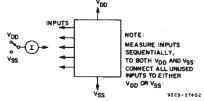


Fig. 16 - Input current test circuit.

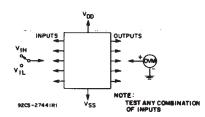
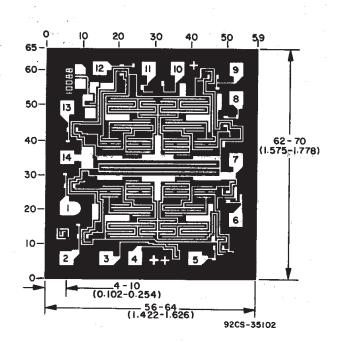
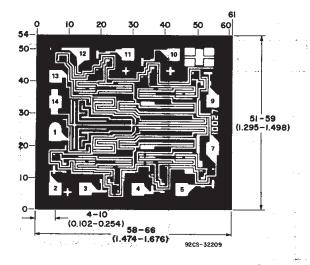


Fig. 17 - Input-voltage test circuit.

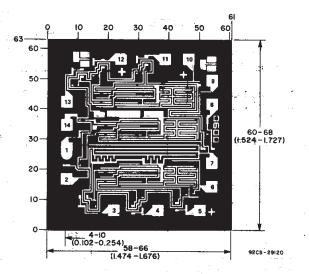
Dimensions in parentheses are in millimeters and are derived from the basic inch dimensions as indicated. Grid graduations are in mils (10<sup>-3</sup> inch).



Chip dimensions and pad layout for CD4071B.



Chip dimensions and pad layout for CD4072B.



Chip dimensions and pad layout for CD4075B.

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